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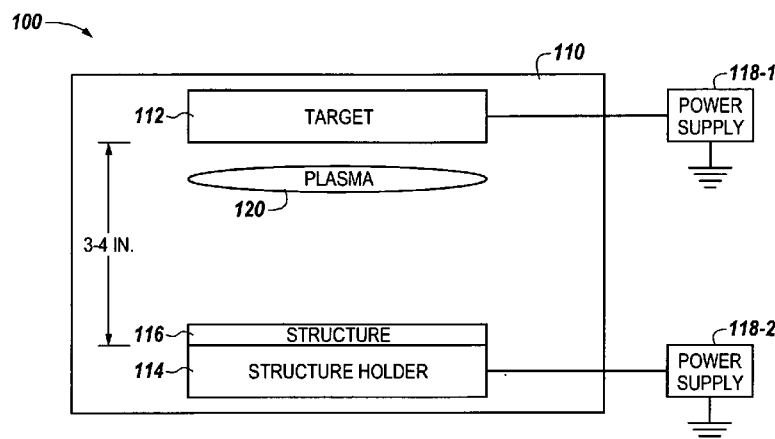
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(54) Title: FORMING MEMORY USING HIGH POWER IMPULSE MAGNETRON SPUTTERING



**Fig. 1**

(57) Abstract: Forming memory using high power impulse magnetron sputtering is described herein. One or more method embodiments include forming a resistive memory material on a structure using high power impulse magnetron sputtering (HIPIMS), wherein the resistive memory material is formed on the structure in an environment having a temperature of approximately 400 degrees Celsius or less.